

# Power MOSFET 750 mAmps, 20 Volts

## N-Channel SOT-23

These miniature surface mount MOSFETs low  $R_{DS(on)}$  assure minimal power loss and conserve energy, making these devices ideal for use in space sensitive power management circuitry. Typical applications are dc-dc converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

### Features

- Low  $R_{DS(on)}$  Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space
- Pb-Free Packages are Available

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	20	Vdc
Gate-to-Source Voltage – Continuous	$V_{GS}$	$\pm 20$	Vdc
Drain Current	$I_D$	750	mA
– Continuous @ $T_A = 25^\circ\text{C}$	$I_{DM}$	2000	
– Pulsed Drain Current ( $t_p \leq 10 \mu\text{s}$ )			
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	400	mW
Operating and Storage Temperature Range	$T_J, T_{stg}$	$-55$ to $150$	$^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	300	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	$T_L$	260	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

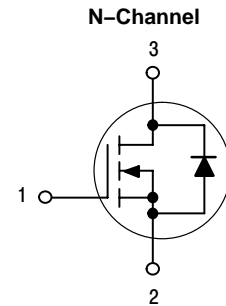


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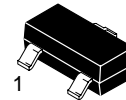
<http://onsemi.com>

**750 mAMPS, 20 VOLTS**

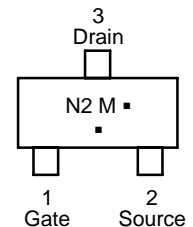
**$R_{DS(on)} = 90 \text{ m}\Omega$**



### MARKING DIAGRAM/ PIN ASSIGNMENT



**SOT-23  
CASE 318  
STYLE 21**



N2 = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping†
MGSF1N02LT1	SOT-23	3000/Tape & Reel
MGSF1N02LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
MGSF1N02LT3	SOT-23	10,000/Tape & Reel
MGSF1N02LT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**Preferred** devices are recommended choices for future use and best overall value.

# MGSF1N02LT1

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 10 μAdc)	V <sub>(BR)DSS</sub>	20	–	–	Vdc
Zero Gate Voltage Drain Current (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 Vdc) (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	I <sub>DSS</sub>	– –	– –	1.0 10	μAdc
Gate-Body Leakage Current (V <sub>GS</sub> = ± 20 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	–	–	±100	nAdc

### ON CHARACTERISTICS (Note 1)

Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μAdc)	V <sub>GS(th)</sub>	1.0	1.7	2.4	Vdc
Static Drain-to-Source On-Resistance (V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 1.2 Adc) (V <sub>GS</sub> = 4.5 Vdc, I <sub>D</sub> = 1.0 Adc)	r <sub>DS(on)</sub>	– –	0.075 0.115	0.090 0.130	Ω

### DYNAMIC CHARACTERISTICS

Input Capacitance	(V <sub>DS</sub> = 5.0 Vdc)	C <sub>iss</sub>	–	125	–	pF
Output Capacitance	(V <sub>DS</sub> = 5.0 Vdc)	C <sub>oss</sub>	–	120	–	
Transfer Capacitance	(V <sub>DG</sub> = 5.0 Vdc)	C <sub>rss</sub>	–	45	–	

### SWITCHING CHARACTERISTICS (Note 2)

Turn-On Delay Time	(V <sub>DD</sub> = 15 Vdc, I <sub>D</sub> = 1.0 Adc, R <sub>L</sub> = 50 Ω)	t <sub>d(on)</sub>	–	2.5	–	ns
Rise Time		t <sub>r</sub>	–	1.0	–	
Turn-Off Delay Time		t <sub>d(off)</sub>	–	16	–	
Fall Time		t <sub>f</sub>	–	8.0	–	
Gate Charge (See Figure 6)		Q <sub>T</sub>	–	6000	–	pC

### SOURCE-DRAIN DIODE CHARACTERISTICS

Continuous Current	I <sub>S</sub>	–	–	0.6	A
Pulsed Current	I <sub>SM</sub>	–	–	0.75	–
Forward Voltage (Note 2)	V <sub>SD</sub>	–	0.8	–	V

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.

## TYPICAL ELECTRICAL CHARACTERISTICS

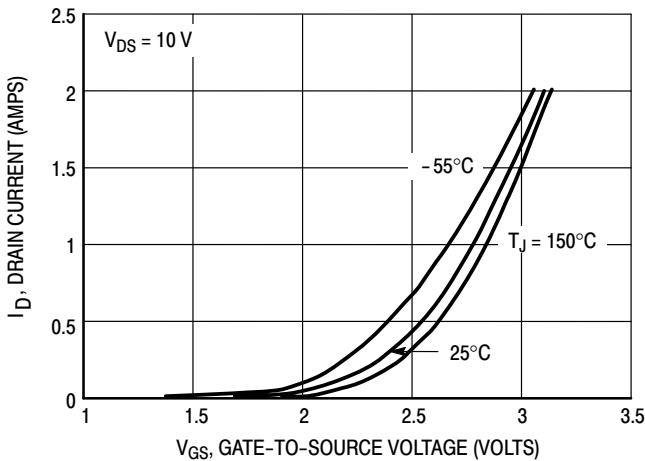


Figure 1. Transfer Characteristics

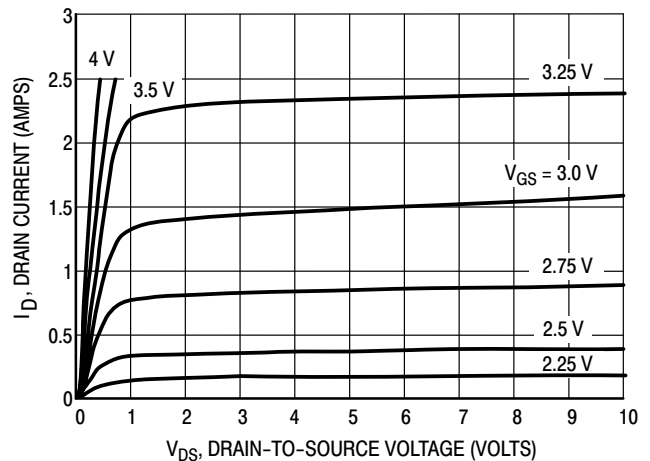


Figure 2. On-Region Characteristics

[查询"MGSF1N02LT1-D"供应商](#)

# TYPICAL ELECTRICAL CHARACTERISTICS

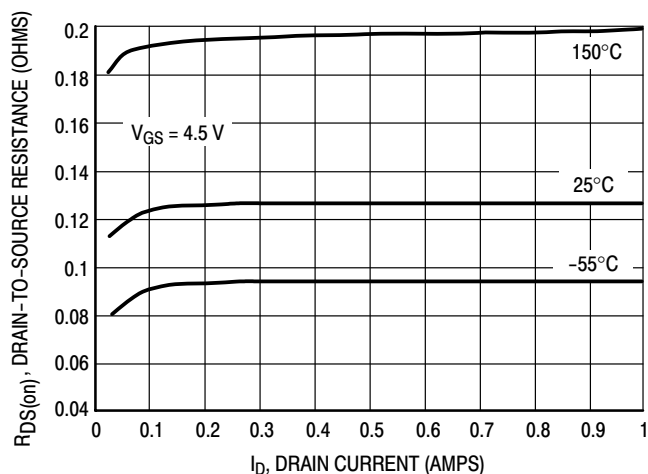


Figure 3. On-Resistance versus Drain Current

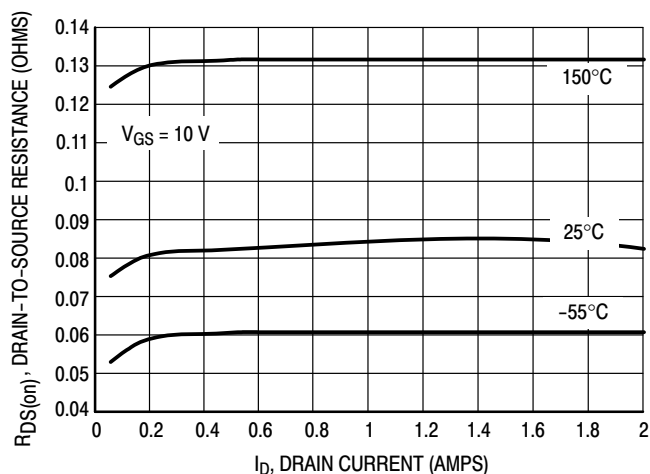


Figure 4. On-Resistance versus Drain Current

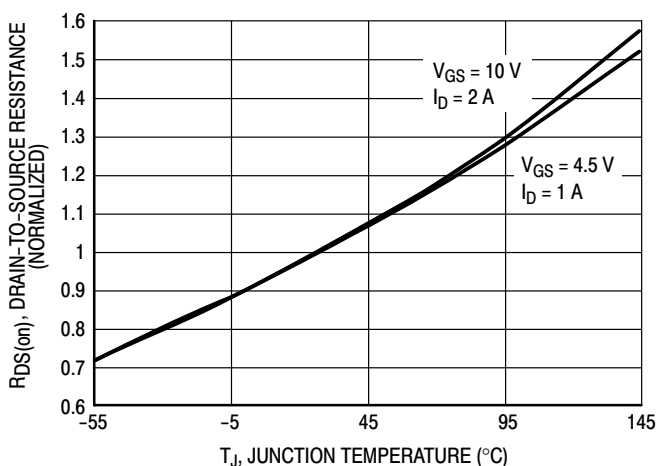


Figure 5. On-Resistance Variation with Temperature

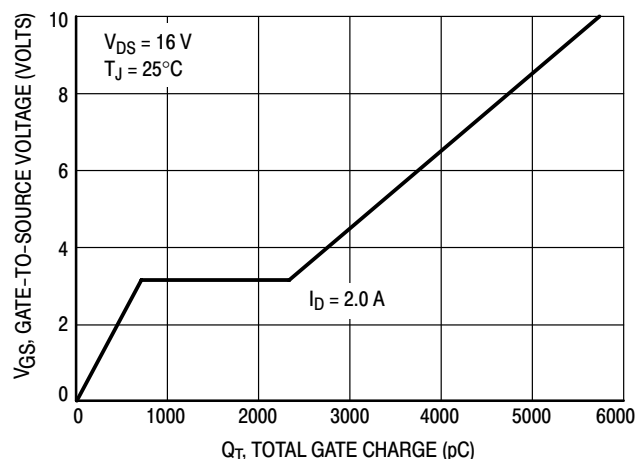


Figure 6. Gate Charge

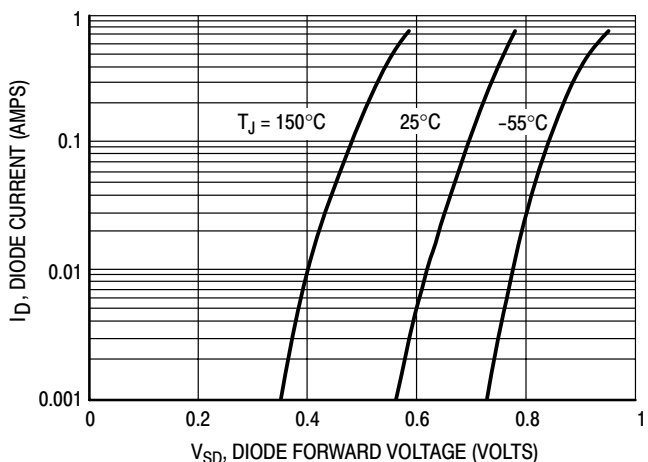


Figure 7. Body Diode Forward Voltage

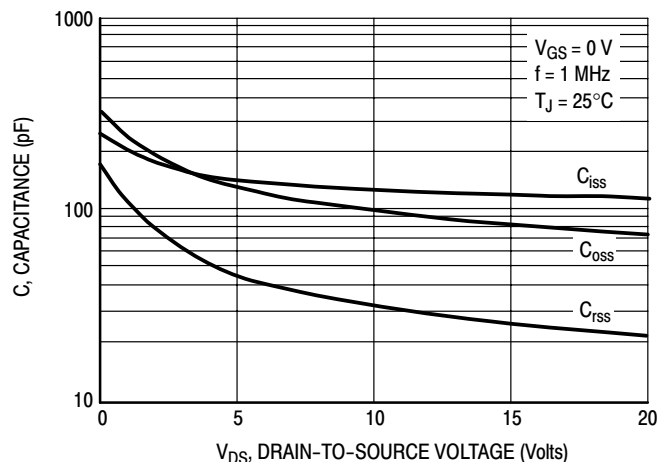


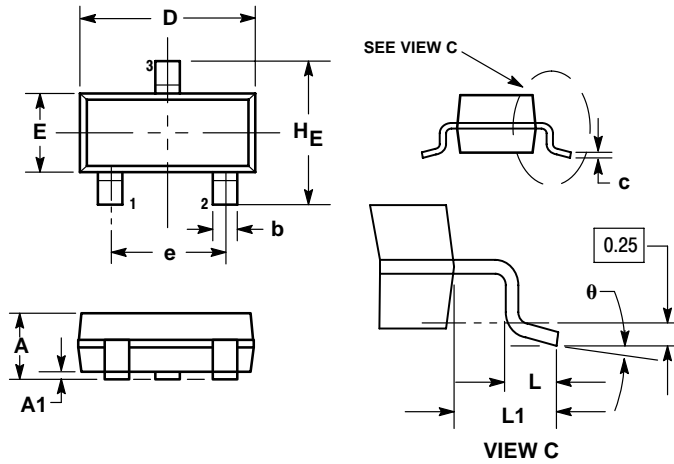
Figure 8. Capacitance

# MGSF1N02LT1

查询"MGSF1N02LT1-D"供应商

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AN



### NOTES:

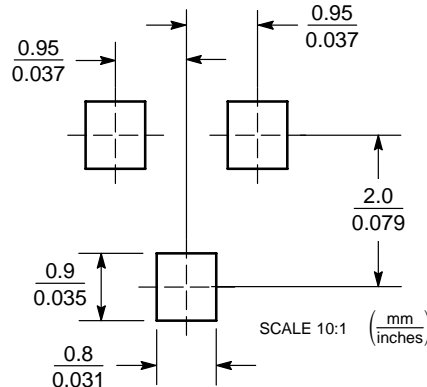
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104


### STYLE 21:

- PIN 1. GATE
- SOURCE
- DRAIN

## SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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